FIG. 1

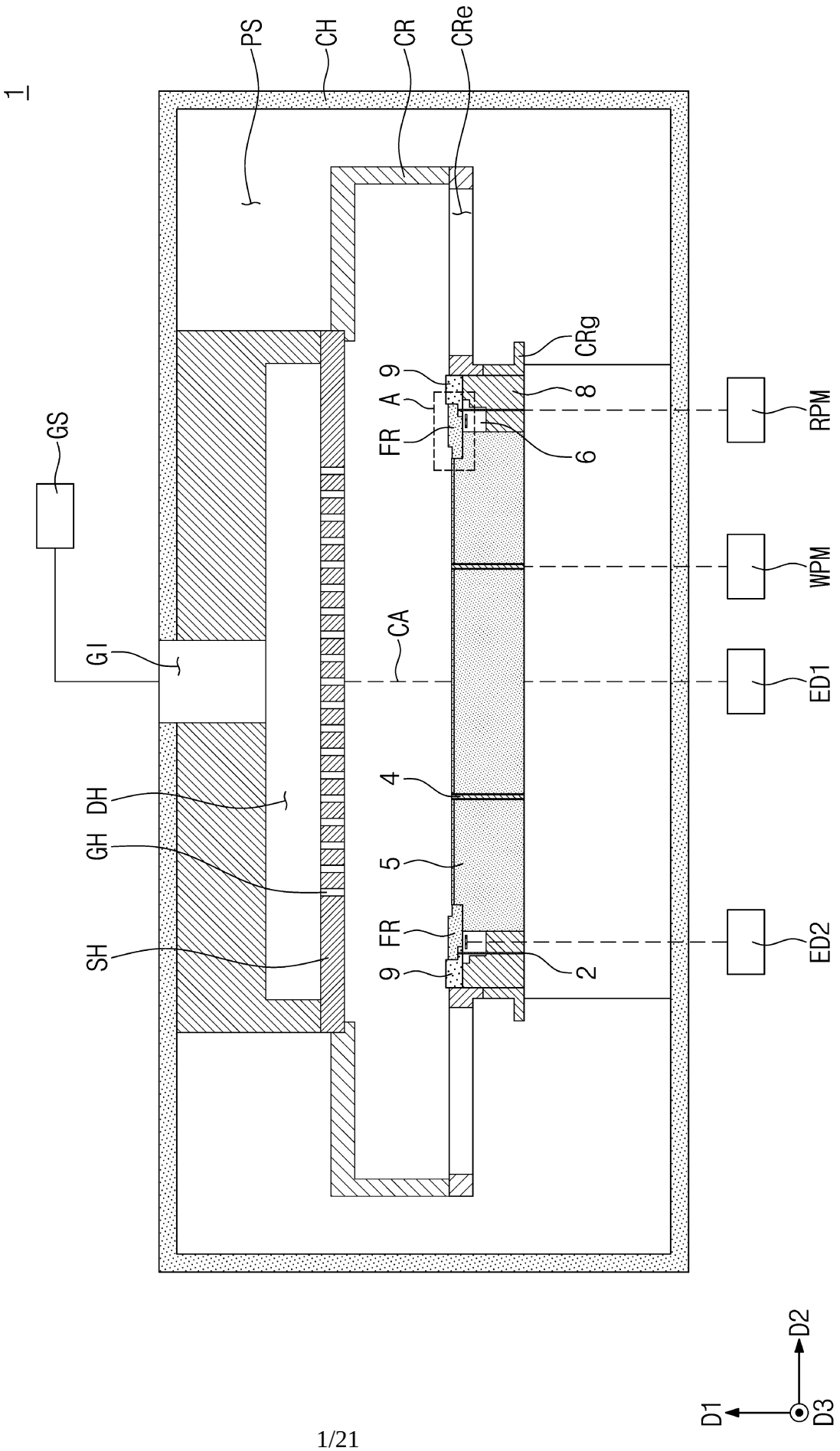

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FIG. 2

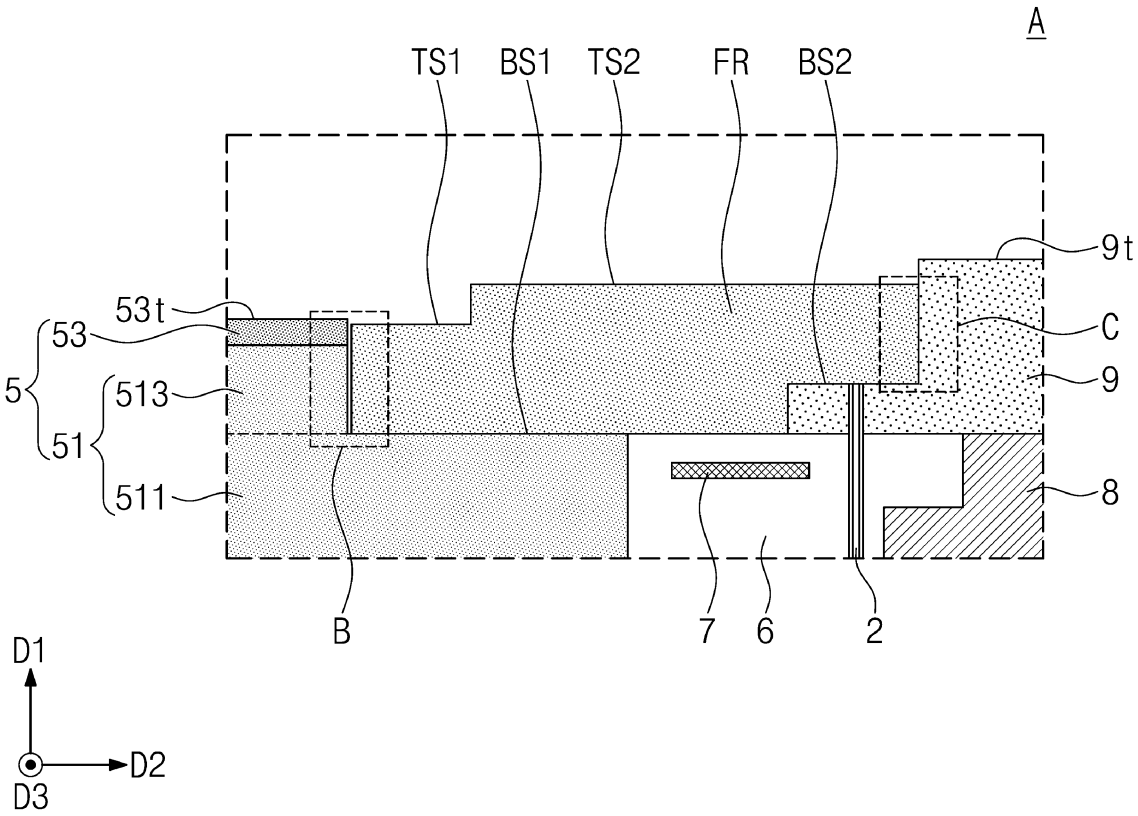


FIG. 3

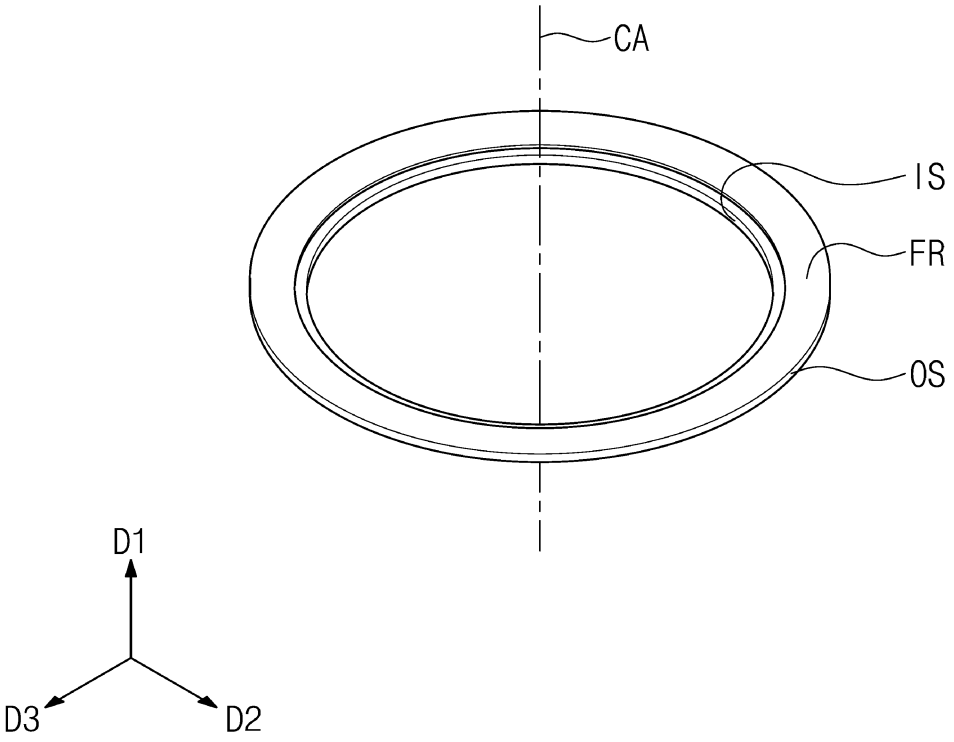


FIG. 4

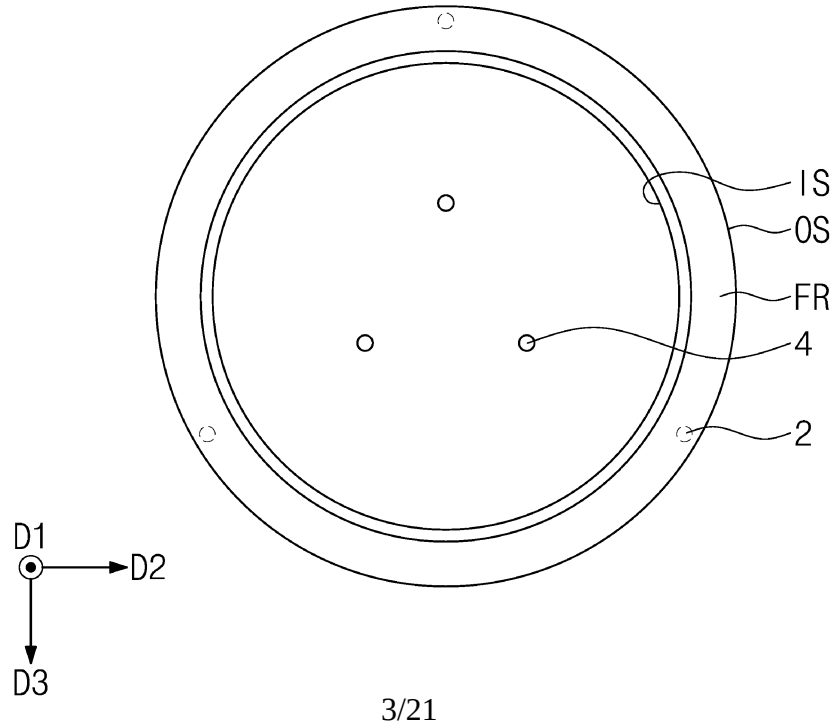


FIG. 5

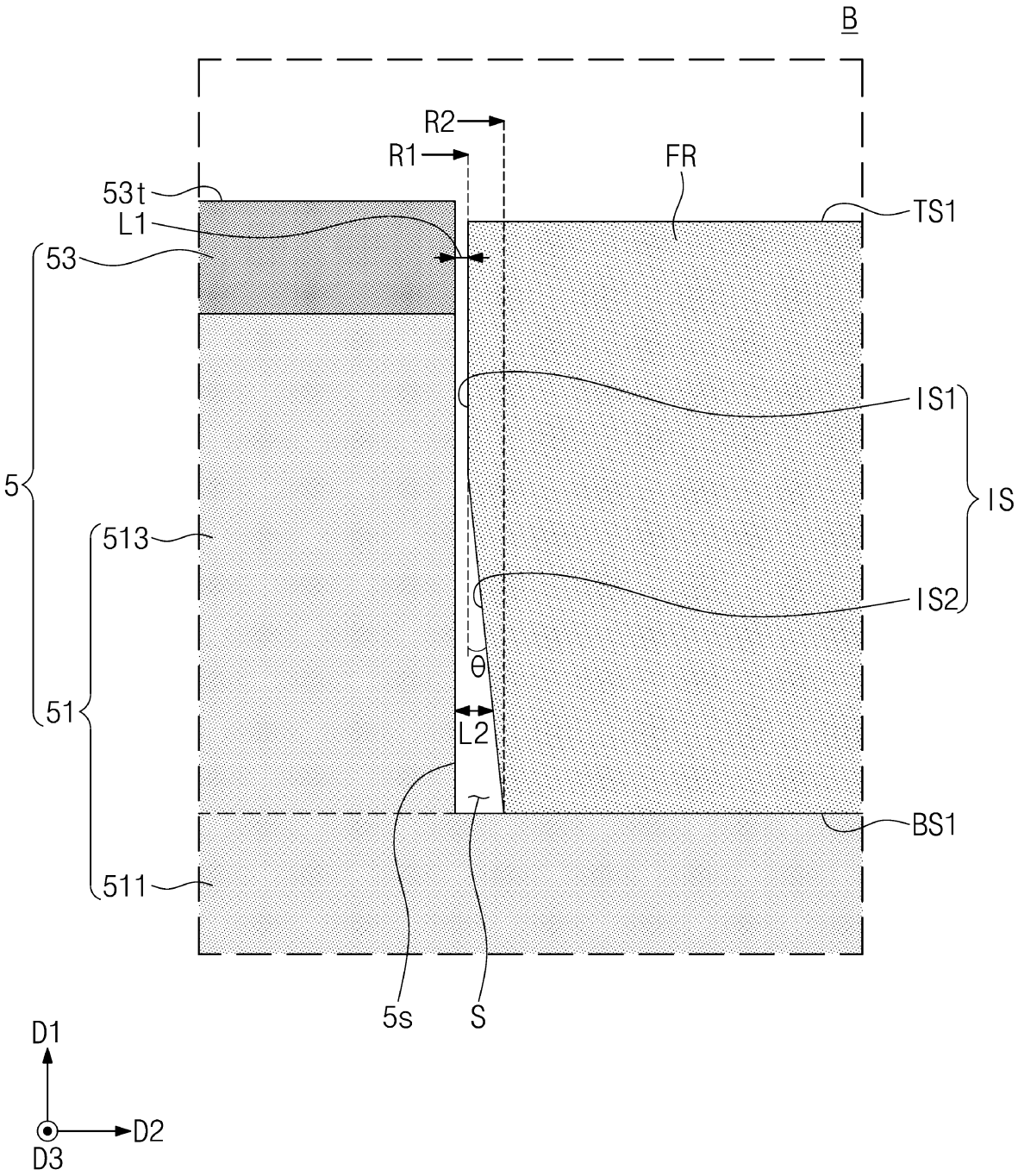


FIG. 6

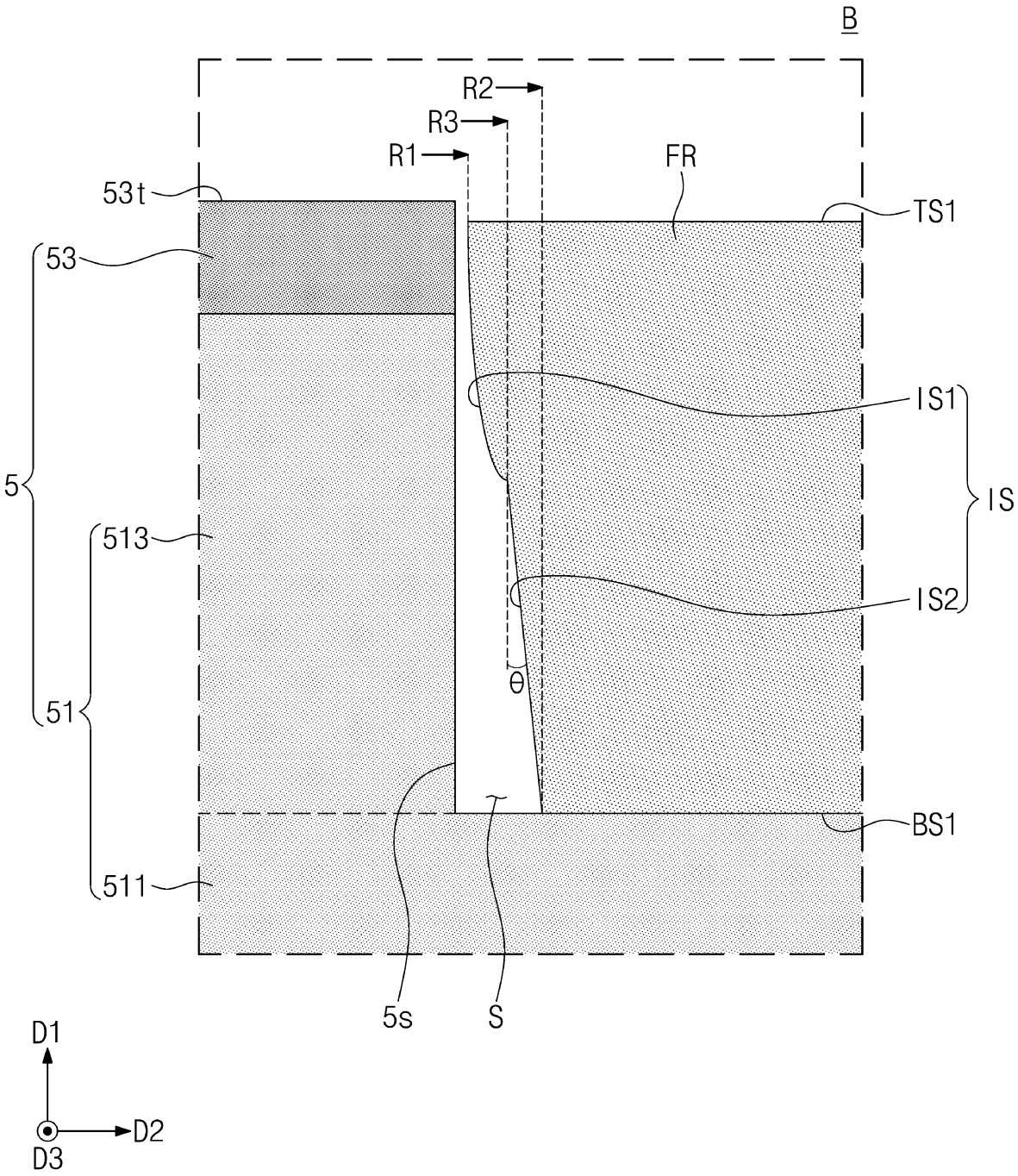


FIG. 7

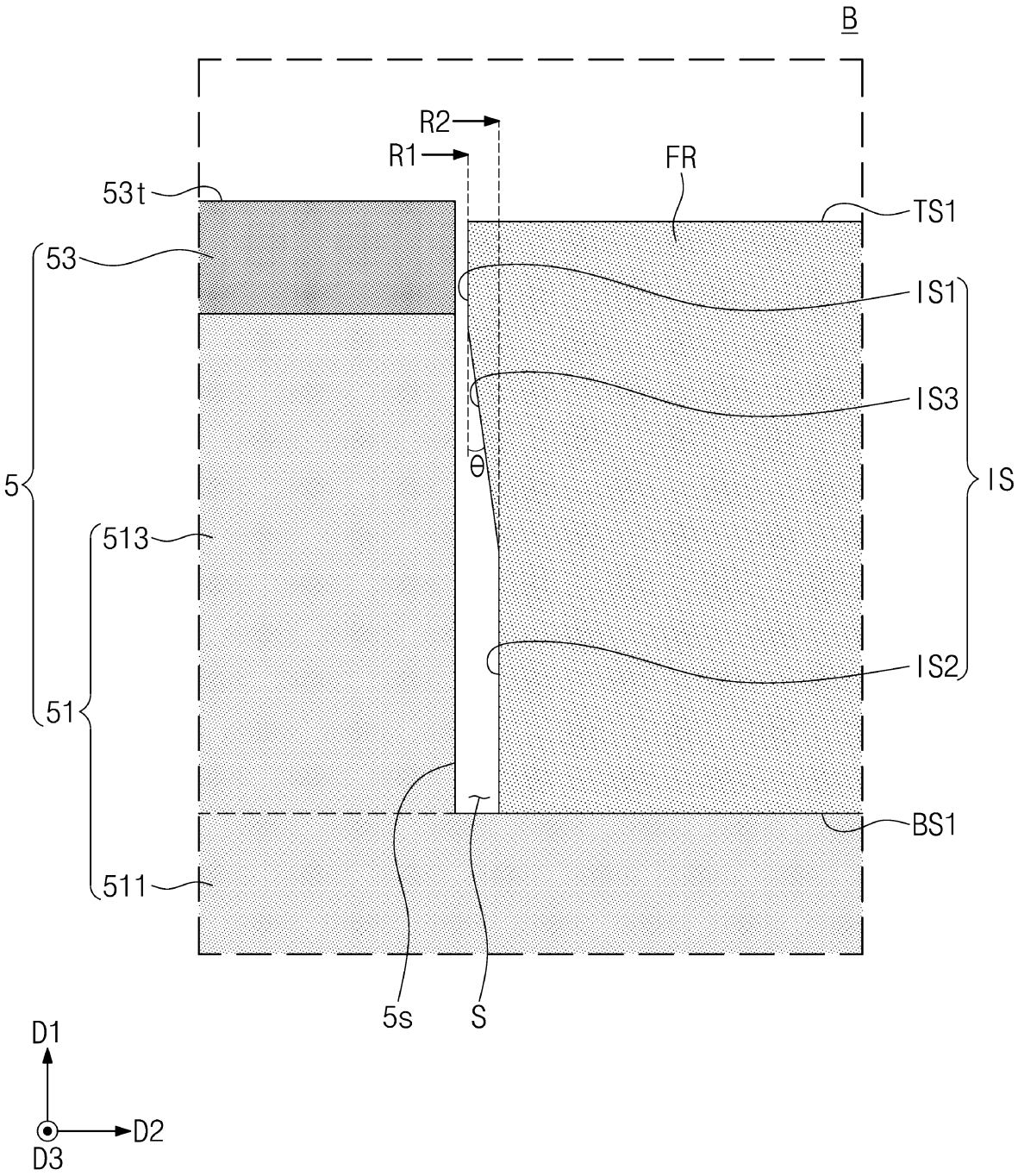


FIG. 8

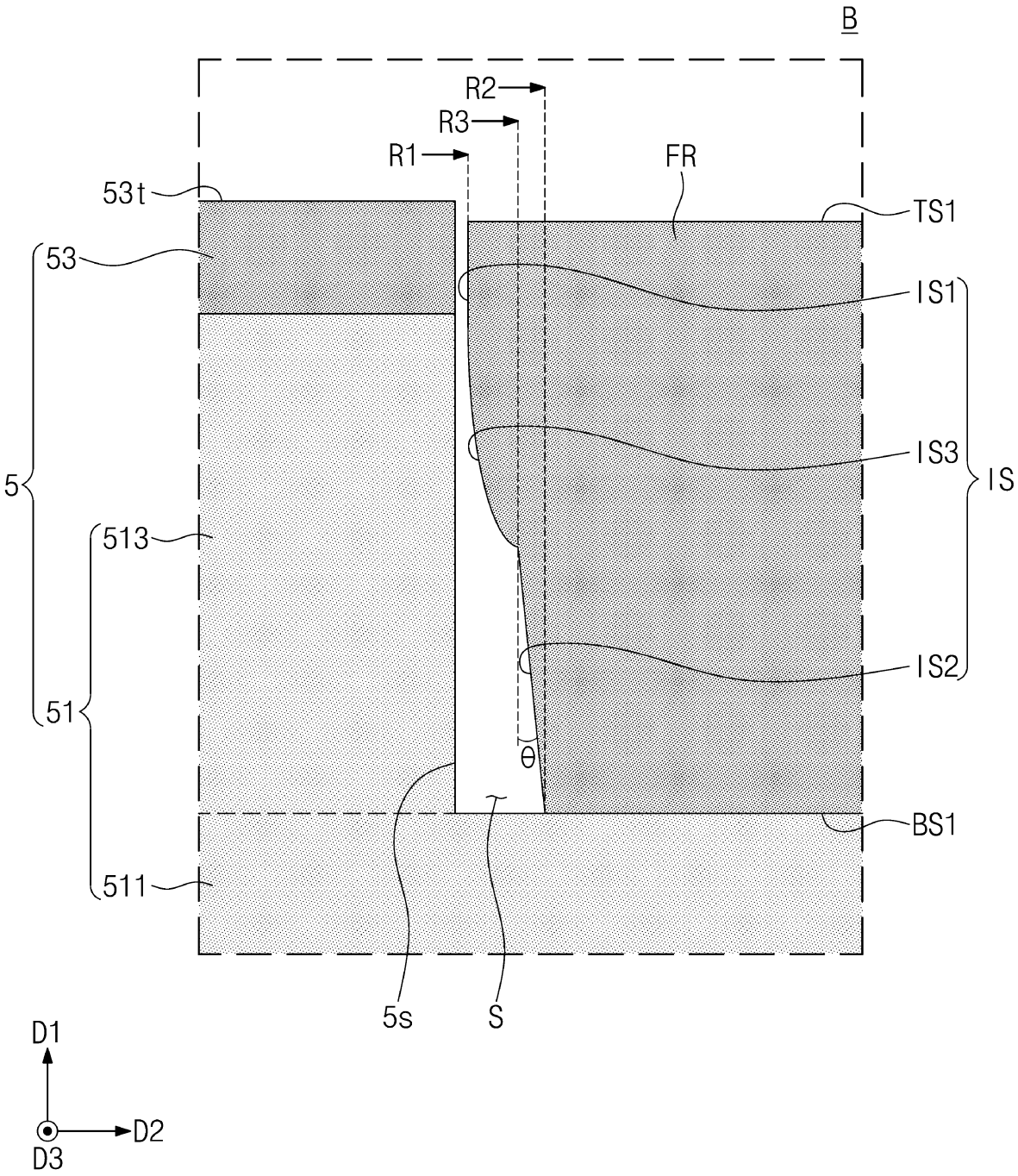

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FIG. 9

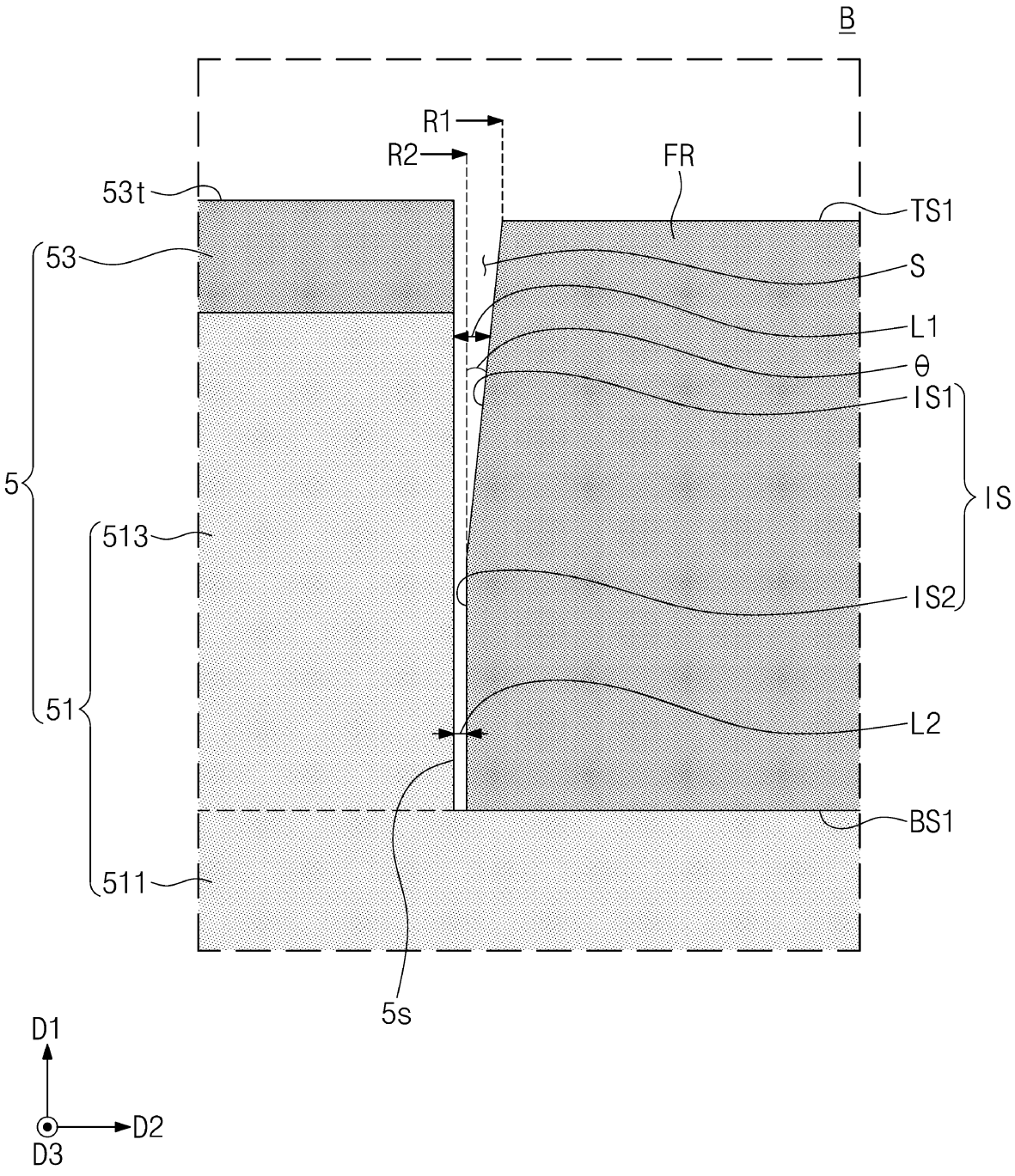


FIG. 10

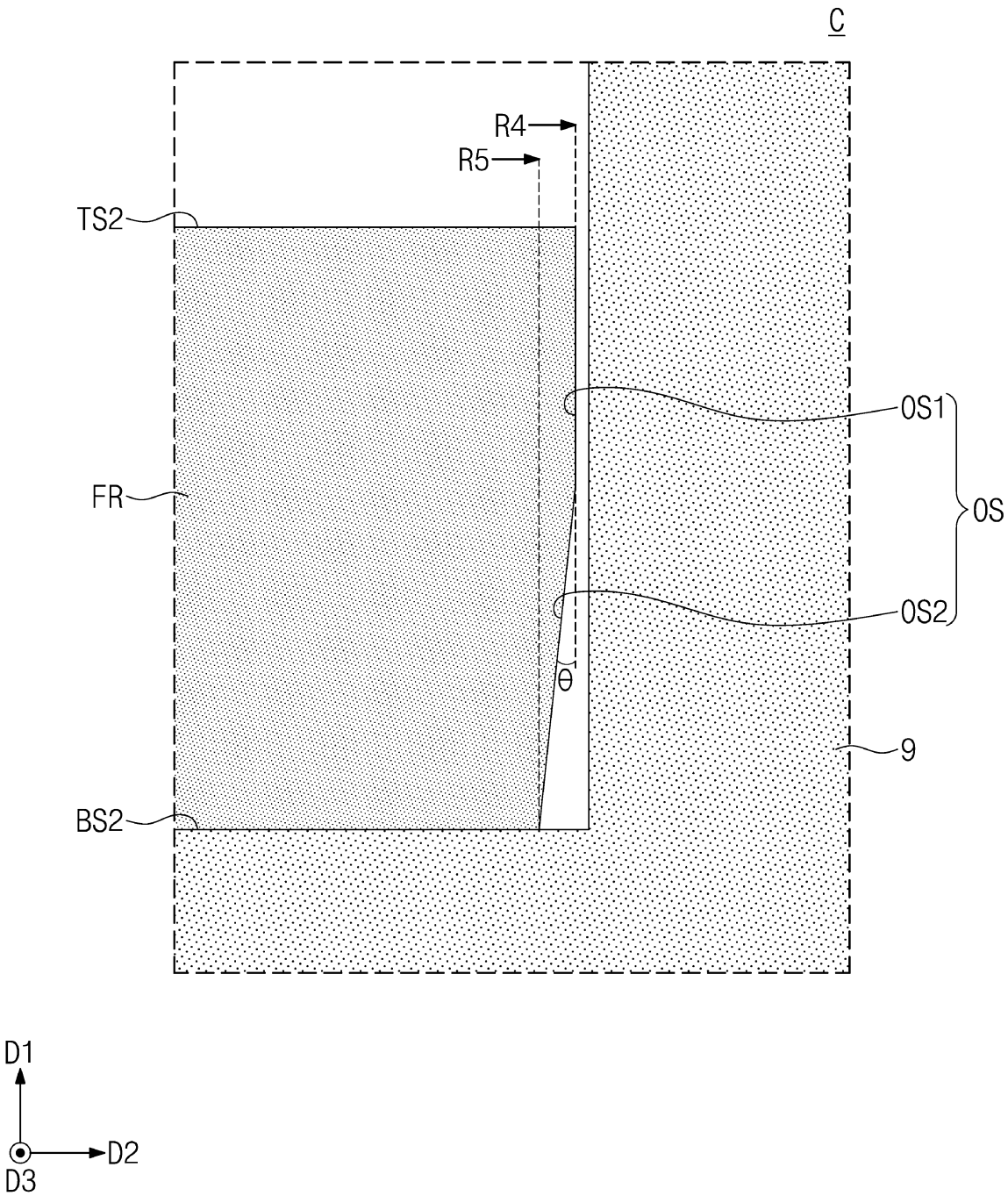


FIG. 11

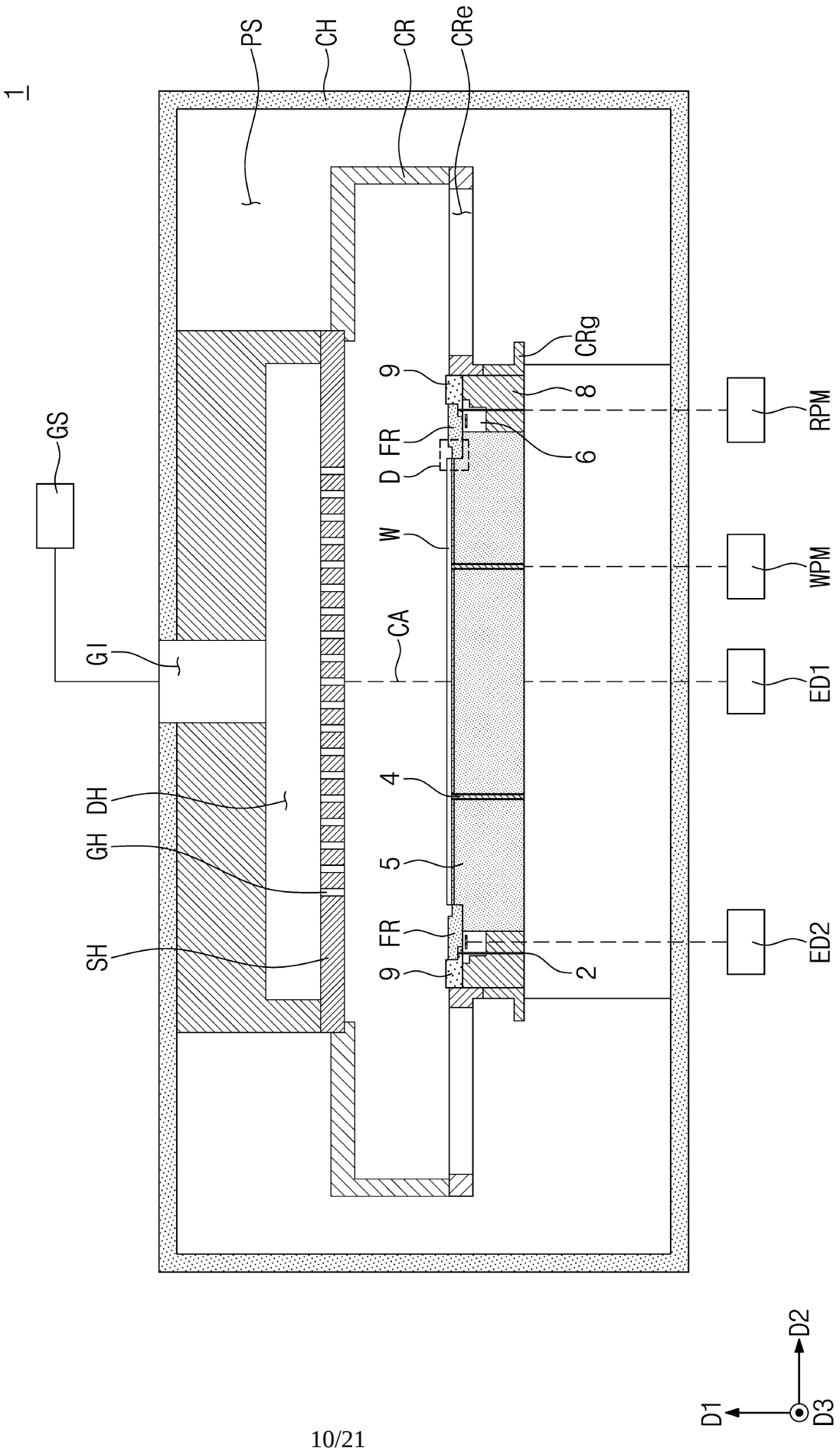

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FIG. 12

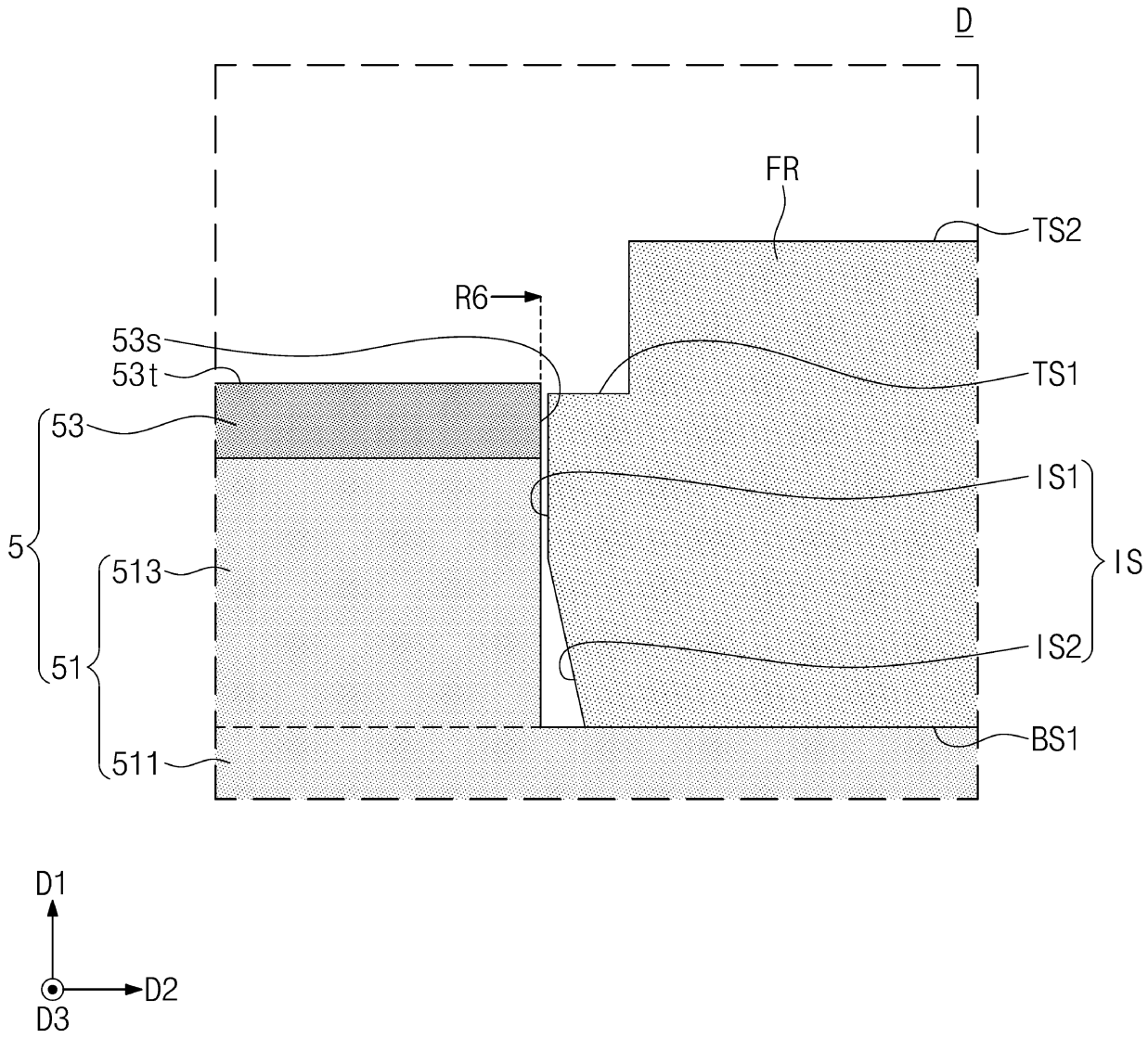


FIG. 13

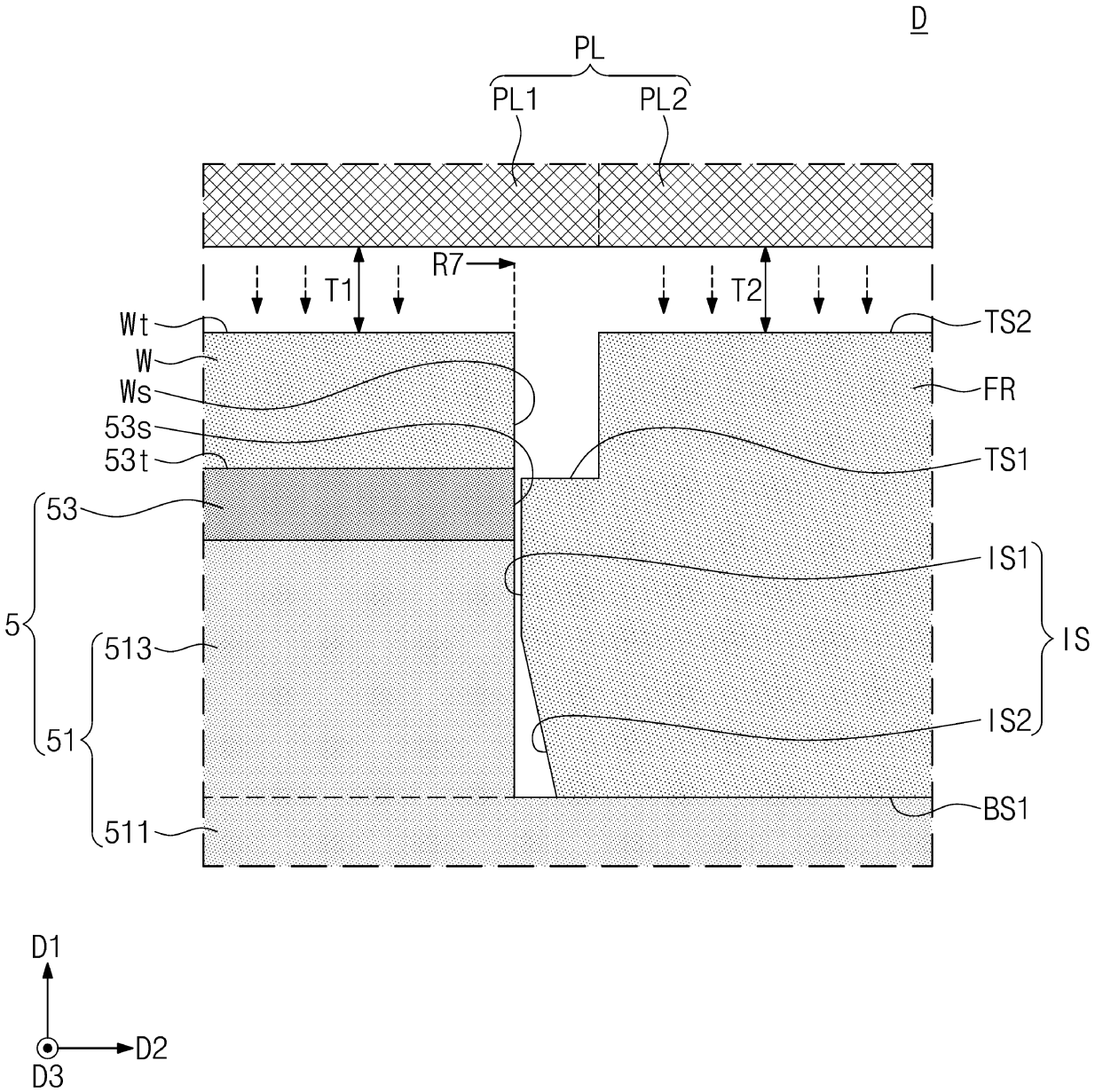

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FIG. 14

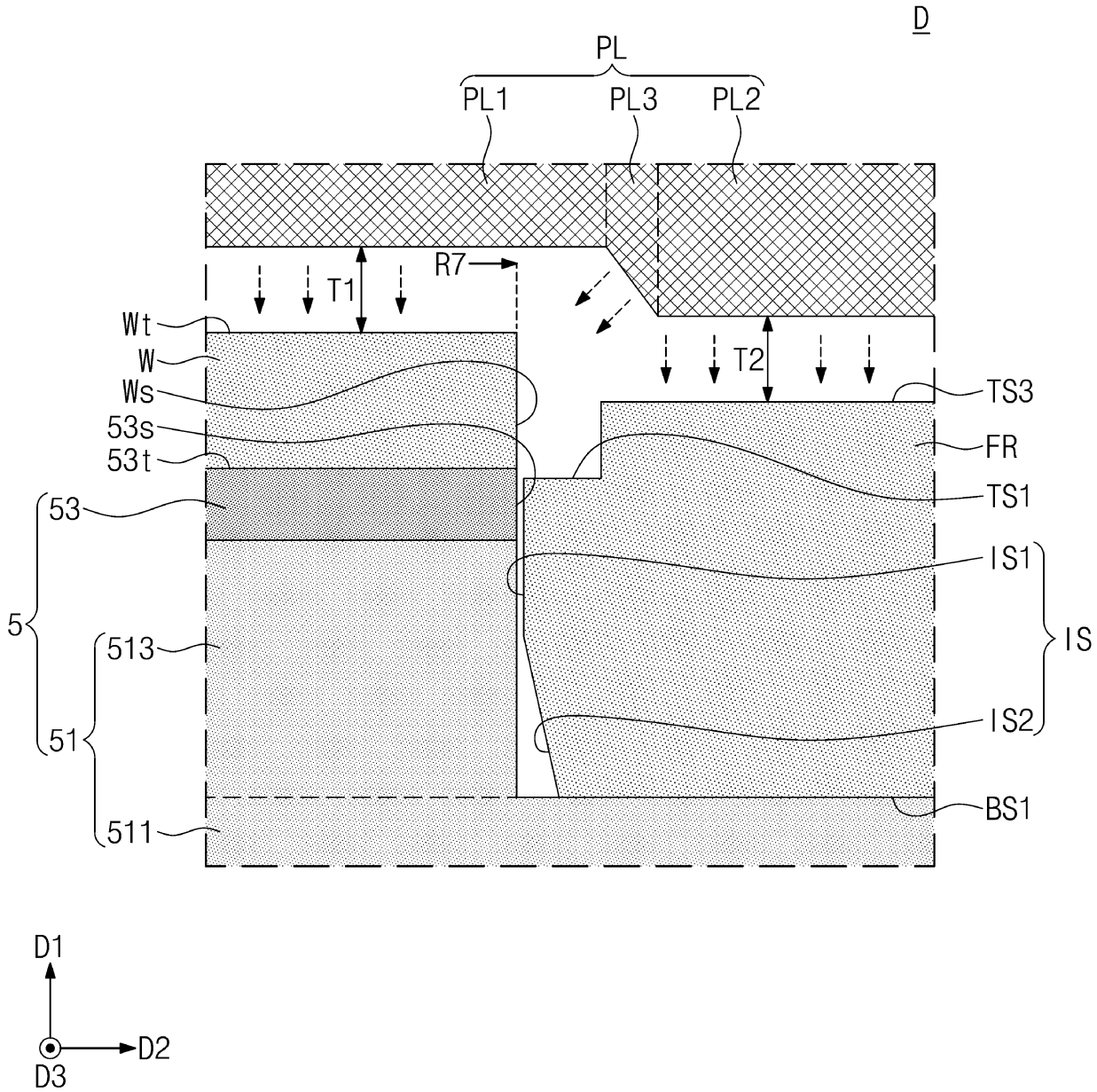

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FIG. 15

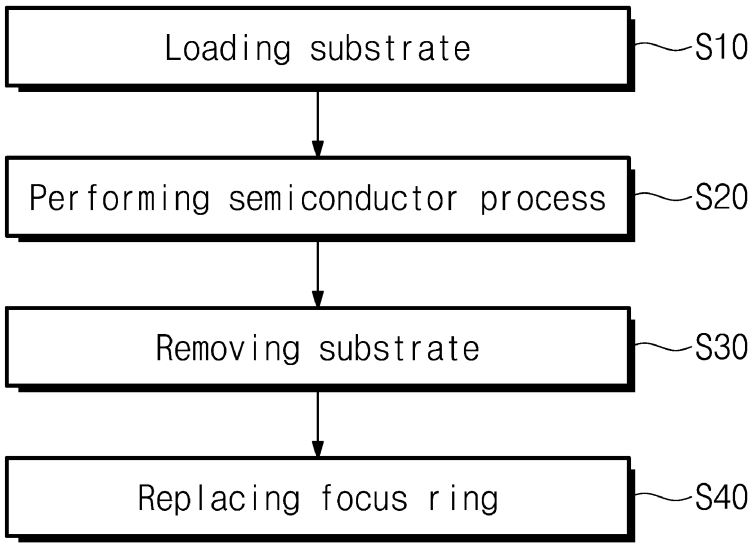

Loading substrate
S10
Performing semiconductor process
S20
Removing substrate
S30
Replacing focus ring
S40

FIG. 16

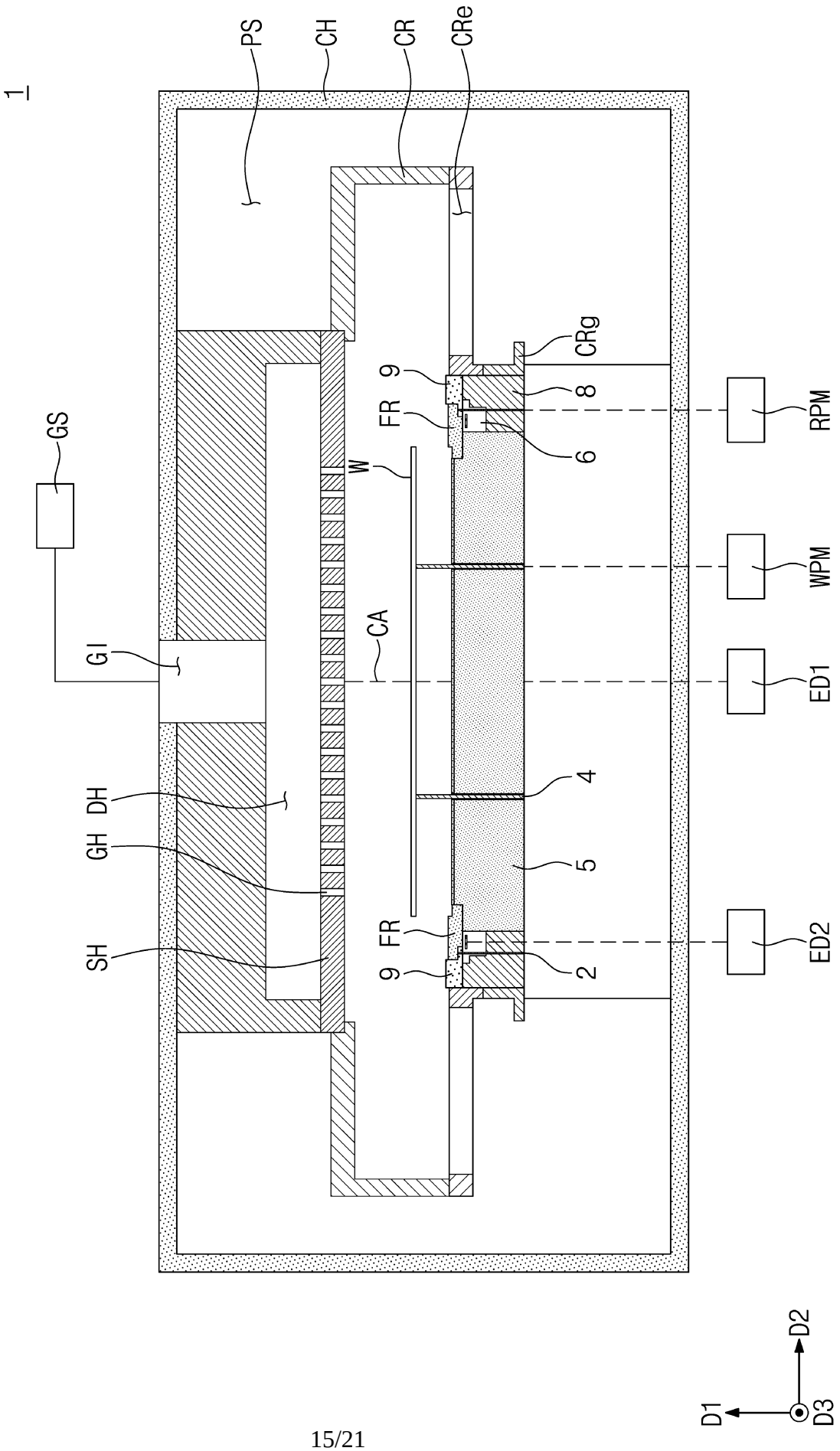

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FIG. 17

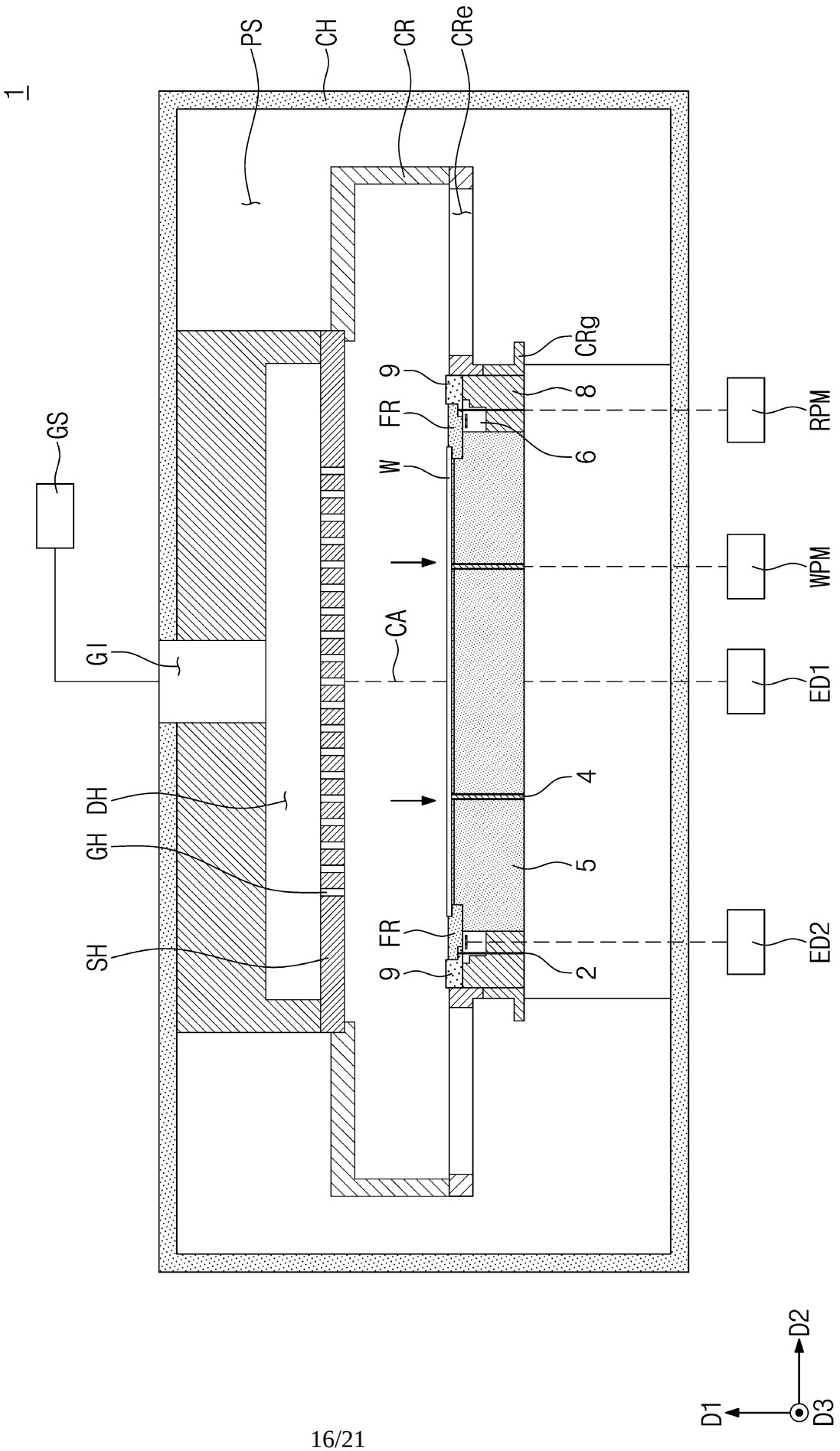

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FIG. 18

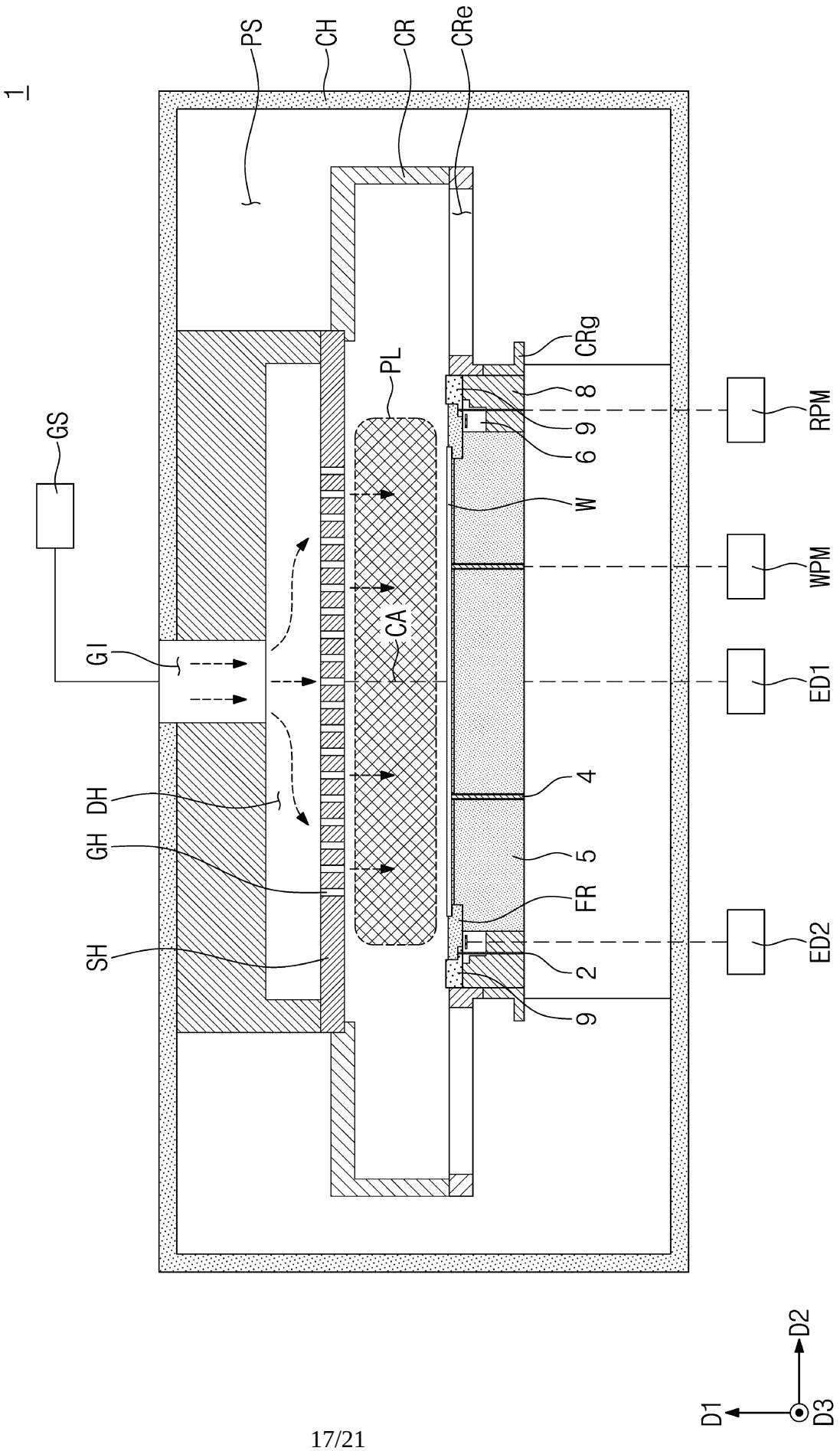

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FIG. 19

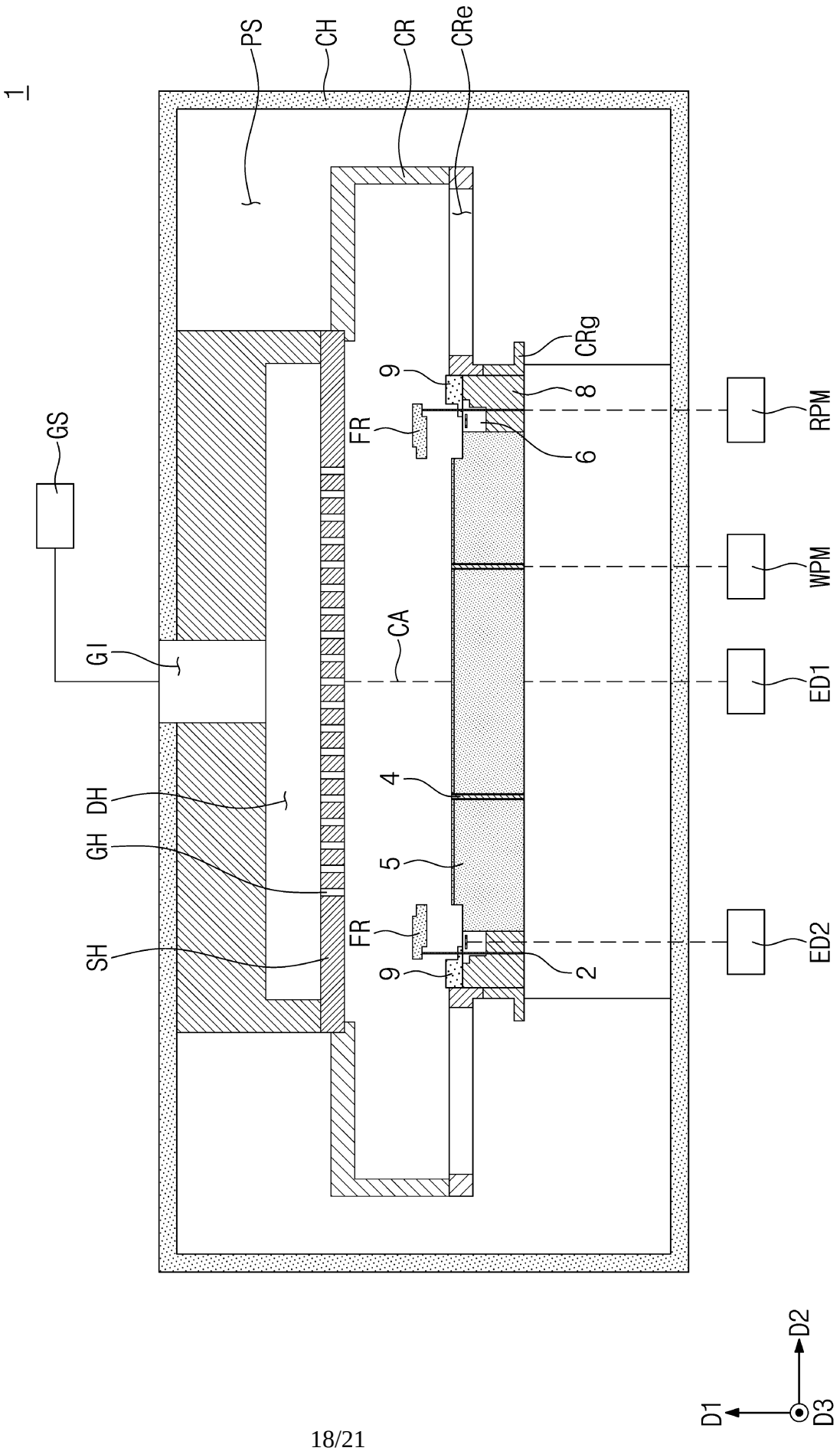

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FIG. 20

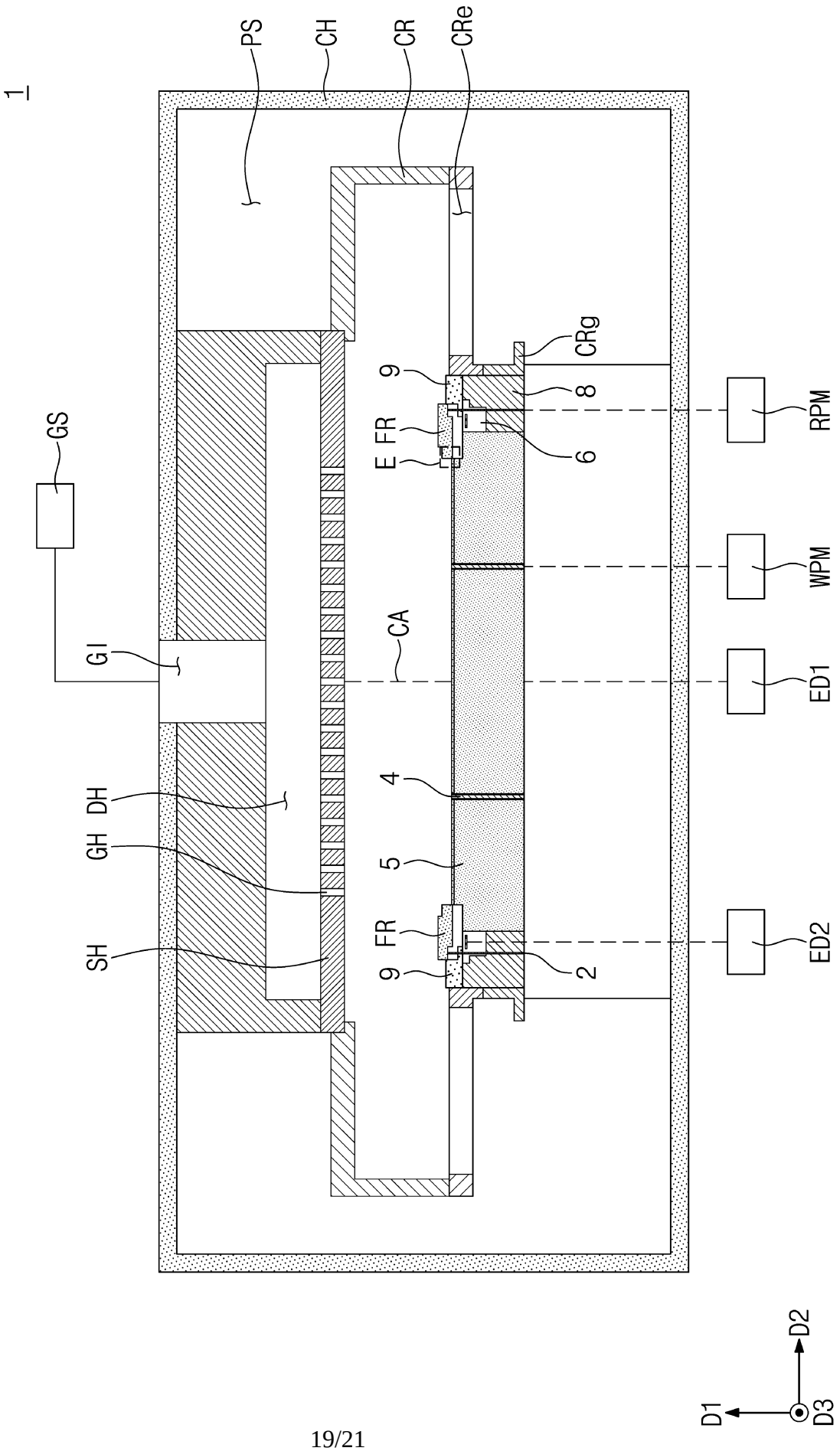

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FIG. 21

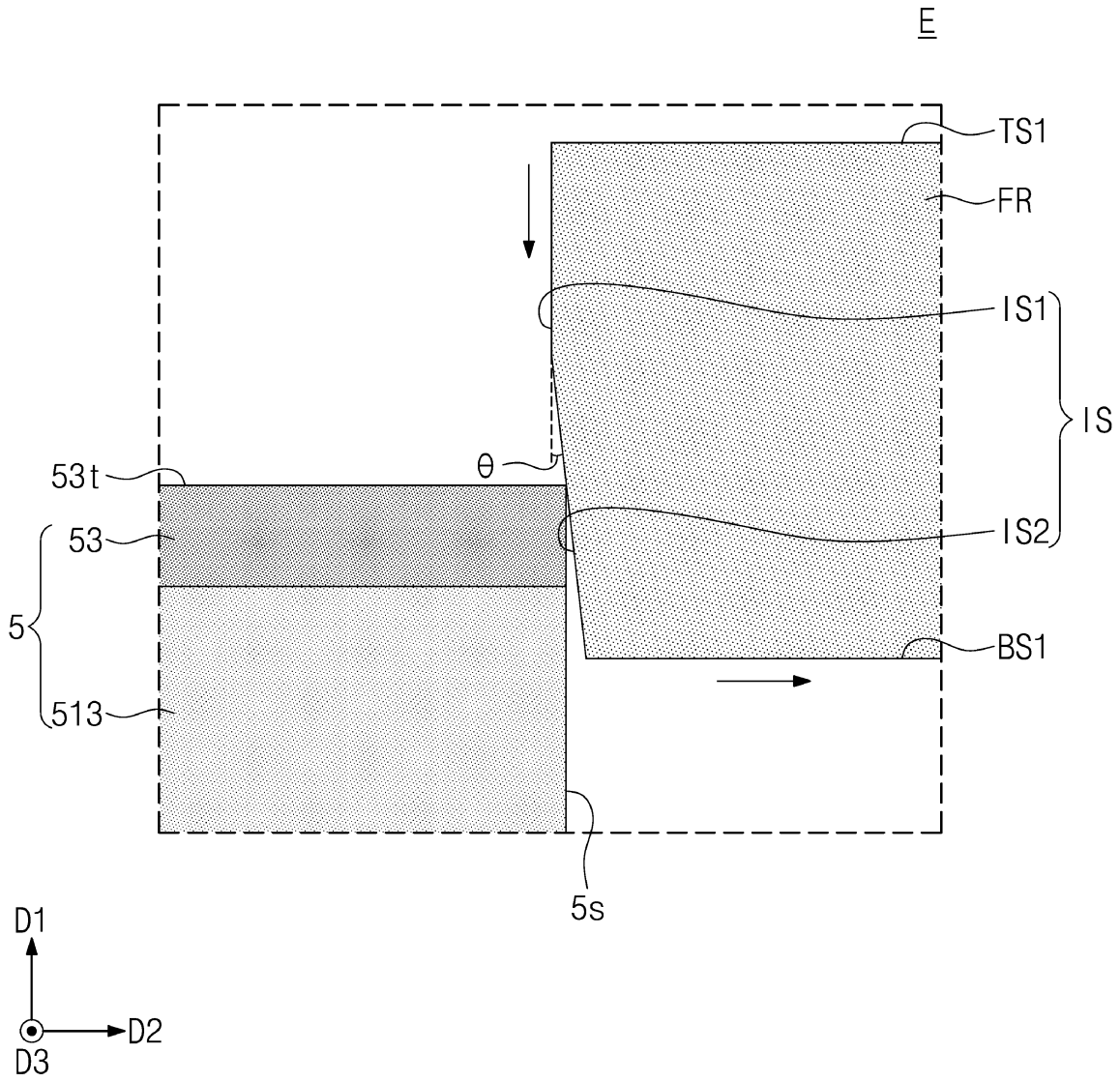


FIG. 22

